

# NTD5802N, NVD5802N

## MOSFET – Power, Single, N-Channel, DPAK 40 V, 101 A

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- MSL 1/260°C
- 100% Avalanche Tested
- NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### Applications

- CPU Power Delivery
- DC-DC Converters
- Motor Driver

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                                                                                                                                    |                      |                       | Symbol                            | Value      | Unit |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------|-----------------------|-----------------------------------|------------|------|
| Drain-to-Source Voltage                                                                                                                                      |                      |                       | V <sub>DSS</sub>                  | 40         | V    |
| Gate-to-Source Voltage                                                                                                                                       |                      |                       | V <sub>GS</sub>                   | ±20        | V    |
| Continuous Drain Current (R <sub>θJC</sub> ) (Note 1)                                                                                                        | Steady State         | T <sub>C</sub> = 25°C | I <sub>D</sub>                    | 101        | A    |
|                                                                                                                                                              |                      | T <sub>C</sub> = 85°C |                                   | 78         |      |
| T <sub>C</sub> = 25°C                                                                                                                                        |                      | P <sub>D</sub>        | 93.75                             | W          |      |
| Continuous Drain Current (R <sub>θJA</sub> ) (Note 1)                                                                                                        |                      | T <sub>A</sub> = 25°C | I <sub>D</sub>                    | 16.4       | A    |
|                                                                                                                                                              |                      | T <sub>A</sub> = 85°C |                                   | 12.7       |      |
| Power Dissipation (R <sub>θJA</sub> ) (Note 1)                                                                                                               |                      | T <sub>A</sub> = 25°C | P <sub>D</sub>                    | 2.5        | W    |
| Pulsed Drain Current                                                                                                                                         | t <sub>p</sub> =10μs | T <sub>A</sub> = 25°C | I <sub>DM</sub>                   | 300        | A    |
| Current Limited by Package                                                                                                                                   |                      | T <sub>A</sub> = 25°C | I <sub>DmaxPkg</sub>              | 45         | A    |
| Operating Junction and Storage Temperature                                                                                                                   |                      |                       | T <sub>J</sub> , T <sub>stg</sub> | -55 to 175 | °C   |
| Source Current (Body Diode)                                                                                                                                  |                      |                       | I <sub>S</sub>                    | 50         | A    |
| Drain to Source dV/dt                                                                                                                                        |                      |                       | dV/dt                             | 6.0        | V/ns |
| Single Pulse Drain-to-Source Avalanche Energy (V <sub>DD</sub> = 32 V, V <sub>GS</sub> = 10 V, L = 0.3 mH, I <sub>L(pk)</sub> = 40 A, R <sub>G</sub> = 25 Ω) |                      |                       | E <sub>AS</sub>                   | 240        | mJ   |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)                                                                                            |                      |                       | T <sub>L</sub>                    | 260        | °C   |

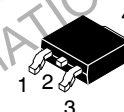
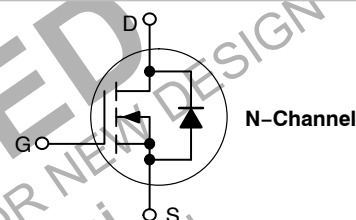
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor®

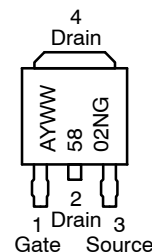
<http://onsemi.com>

| $V_{(BR)DSS}$ | $R_{DS(on)}$           | $I_D$ |
|---------------|------------------------|-------|
| 40 V          | 4.4 m $\Omega$ @ 10 V  | 101 A |
|               | 7.8 m $\Omega$ @ 5.0 V | 50 A  |



CASE 369C  
DPAK  
(Bent Lead)  
STYLE 2

### MARKING DIAGRAMS & PIN ASSIGNMENT



A = Assembly Location\*  
Y = Year  
WW = Work Week  
5802N = Device Code  
G = Pb-Free Package

\* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

**THERMAL RESISTANCE MAXIMUM RATINGS**

| Parameter                                   | Symbol          | Value | Unit |
|---------------------------------------------|-----------------|-------|------|
| Junction-to-Case (Drain)                    | $R_{\theta JC}$ | 1.6   | °C/W |
| Junction-to-Ambient - Steady State (Note 1) | $R_{\theta JA}$ | 60    |      |
| Junction-to-Ambient - Steady State (Note 2) | $R_{\theta JA}$ | 105   |      |

1. Surface-mounted on FR4 board using 1 in sq pad size, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

**ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

**OFF CHARACTERISTICS**

|                                                           |                   |                                                    |                           |    |           |               |
|-----------------------------------------------------------|-------------------|----------------------------------------------------|---------------------------|----|-----------|---------------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 10\text{ }\mu\text{A}$ | 40                        |    |           | V             |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ |                                                    |                           | 40 |           | mV/°C         |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$        | $T_J = 25^\circ\text{C}$  |    | 1.0       | $\mu\text{A}$ |
|                                                           |                   |                                                    | $T_J = 150^\circ\text{C}$ |    | 50        |               |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$    |                           |    | $\pm 100$ | nA            |

**ON CHARACTERISTICS** (Note 3)

|                                            |                  |                                                 |     |      |     |            |
|--------------------------------------------|------------------|-------------------------------------------------|-----|------|-----|------------|
| Gate Threshold Voltage                     | $V_{GS(TH)}$     | $V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$ | 1.5 |      | 3.5 | V          |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ |                                                 |     | -7.4 |     | mV/°C      |
| Drain-to-Source On Resistance              | $R_{DS(on)}$     | $V_{GS} = 10\text{ V}, I_D = 50\text{ A}$       |     | 3.6  | 4.4 | m $\Omega$ |
|                                            |                  | $V_{GS} = 5.0\text{ V}, I_D = 50\text{ A}$      |     | 6.5  | 7.8 |            |
| Forward Transconductance                   | $g_{FS}$         | $V_{DS} = 15\text{ V}, I_D = 15\text{ A}$       |     | 16.8 |     | S          |

**CHARGES AND CAPACITANCES**

|                              |              |                                                                 |  |      |     |    |
|------------------------------|--------------|-----------------------------------------------------------------|--|------|-----|----|
| Input Capacitance            | $C_{iss}$    | $V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 12\text{ V}$ |  | 5300 |     | pF |
| Output Capacitance           | $C_{oss}$    |                                                                 |  | 850  |     |    |
| Reverse Transfer Capacitance | $C_{rss}$    |                                                                 |  | 550  |     |    |
| Input Capacitance            | $C_{iss}$    | $V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 25\text{ V}$ |  | 5025 |     | pF |
| Output Capacitance           | $C_{oss}$    |                                                                 |  | 580  |     |    |
| Reverse Transfer Capacitance | $C_{rss}$    |                                                                 |  | 400  |     |    |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 50\text{ A}$ |  | 75   | 100 | nC |
| Threshold Gate Charge        | $Q_{G(TH)}$  |                                                                 |  | 6.0  |     |    |
| Gate-to-Source Charge        | $Q_{GS}$     |                                                                 |  | 18   |     |    |
| Gate-to-Drain Charge         | $Q_{GD}$     |                                                                 |  | 15   |     |    |

**SWITCHING CHARACTERISTICS** (Note 4)

|                     |              |                                                                                          |  |     |  |    |
|---------------------|--------------|------------------------------------------------------------------------------------------|--|-----|--|----|
| Turn-On Delay Time  | $t_{d(on)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}, I_D = 50\text{ A}, R_G = 2.0\text{ }\Omega$ |  | 14  |  | ns |
| Rise Time           | $t_r$        |                                                                                          |  | 52  |  |    |
| Turn-Off Delay Time | $t_{d(off)}$ |                                                                                          |  | 39  |  |    |
| Fall Time           | $t_f$        |                                                                                          |  | 8.5 |  |    |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Switching characteristics are independent of operating junction temperatures.

# NTD5802N, NVD5802N

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

| Parameter                                 | Symbol   | Test Condition                                                               | Min | Typ | Max | Unit |
|-------------------------------------------|----------|------------------------------------------------------------------------------|-----|-----|-----|------|
| <b>DRAIN-SOURCE DIODE CHARACTERISTICS</b> |          |                                                                              |     |     |     |      |
| Forward Diode Voltage                     | $V_{SD}$ | $V_{GS} = 0\text{ V}, I_S = 50\text{ A}$                                     |     | 0.9 | 1.2 | V    |
|                                           |          | $V_{GS} = 0\text{ V}, I_S = 20\text{ A}$                                     |     | 0.8 | 1.0 |      |
| Reverse Recovery Time                     | $t_{RR}$ | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 50\text{ A}$ |     | 25  |     | ns   |
| Charge Time                               | $t_a$    |                                                                              |     | 15  |     |      |
| Discharge Time                            | $t_b$    |                                                                              |     | 10  |     |      |
| Reverse Recovery Charge                   | $Q_{RR}$ |                                                                              |     | 15  |     | nC   |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

4. Switching characteristics are independent of operating junction temperatures.

**DISCONTINUED**  
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN  
PLEASE CONTACT YOUR onsemi  
REPRESENTATIVE FOR INFORMATION

TYPICAL PERFORMANCE CHARACTERISTICS

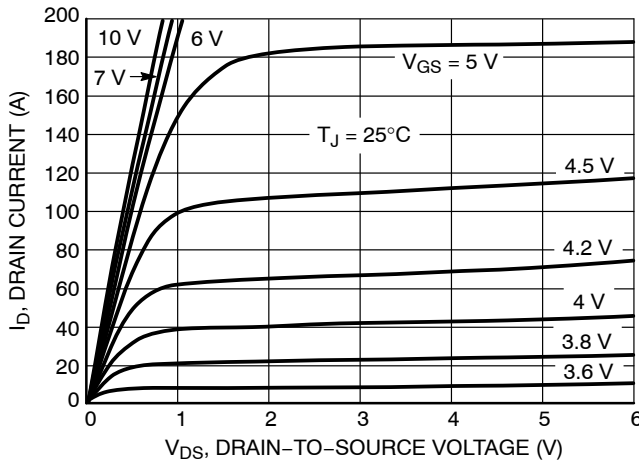


Figure 1. On-Region Characteristics

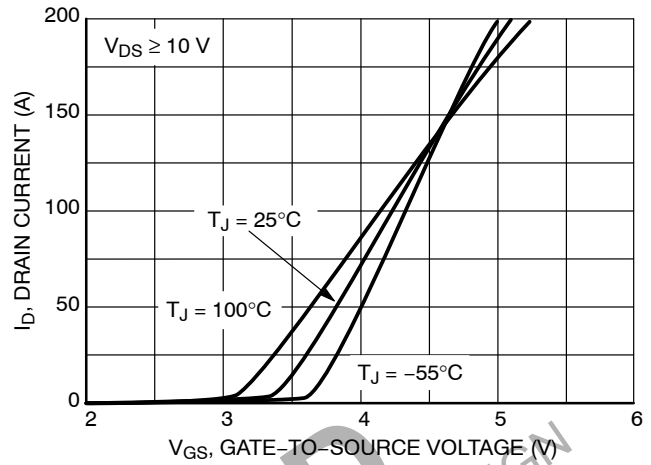


Figure 2. Transfer Characteristics

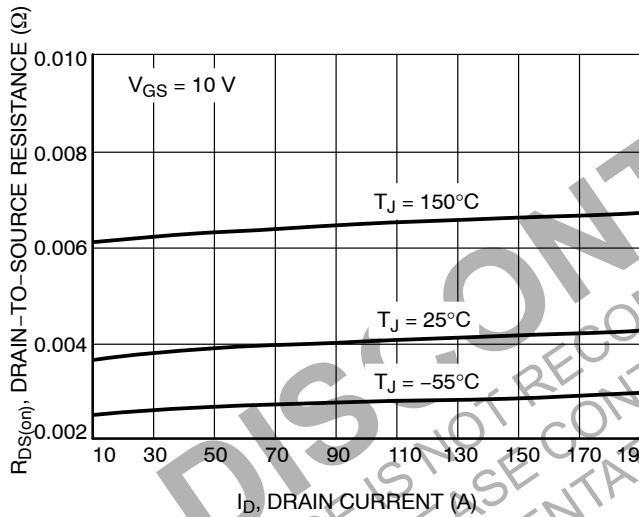


Figure 3. On-Resistance vs. Drain Current

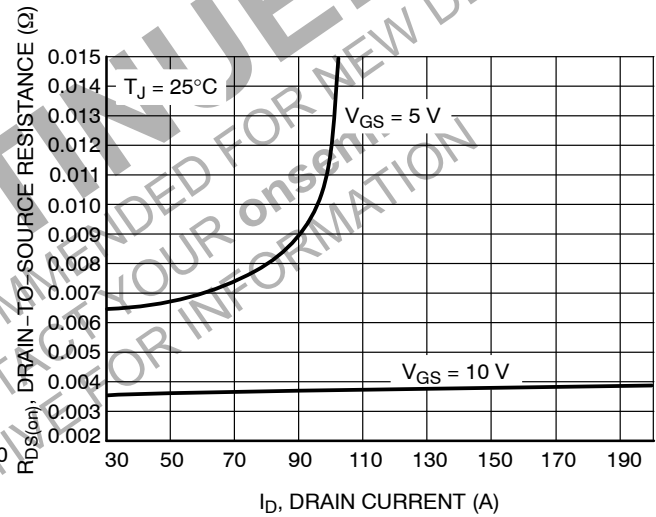


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

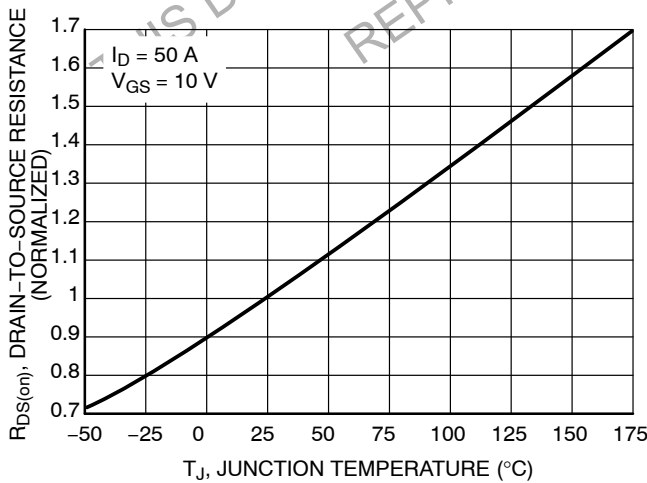


Figure 5. On-Resistance Variation with Temperature

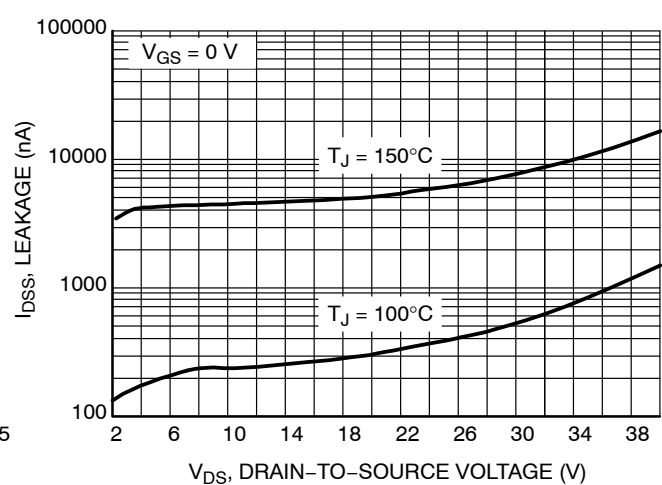


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CHARACTERISTICS

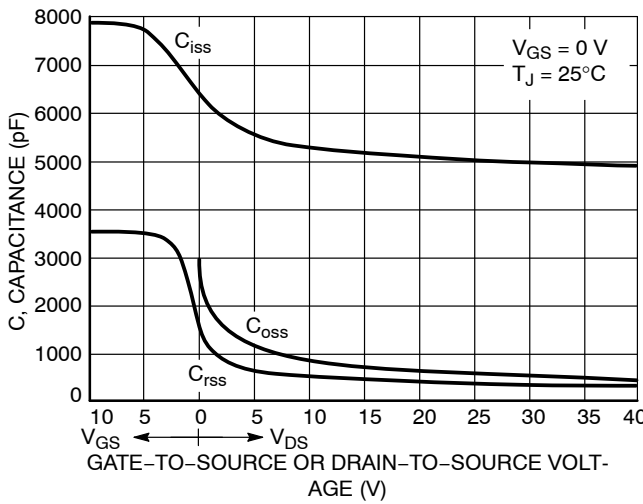


Figure 7. Capacitance Variation

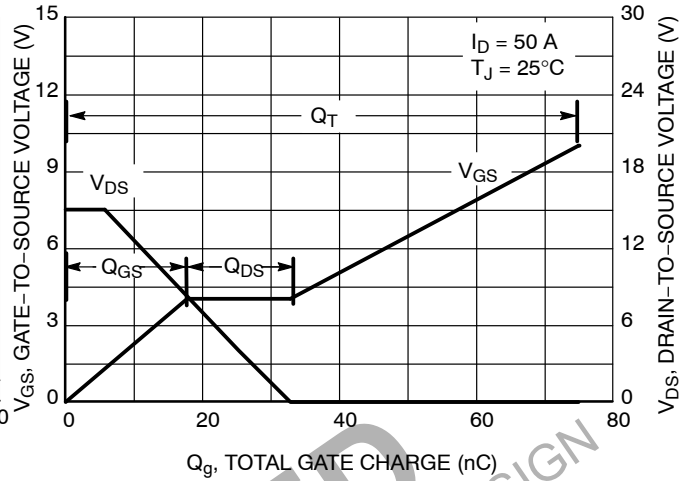


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

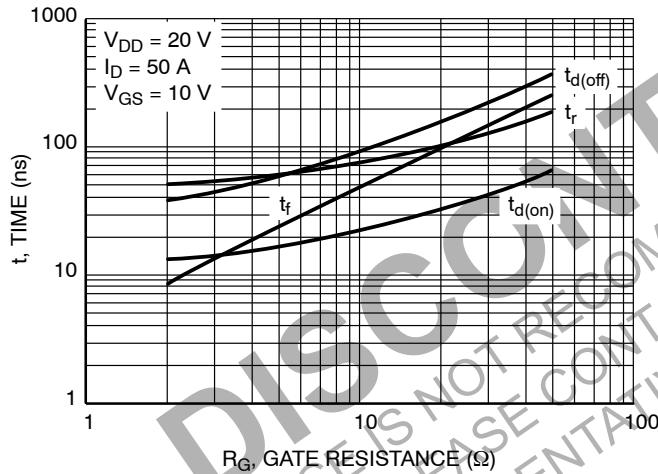


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

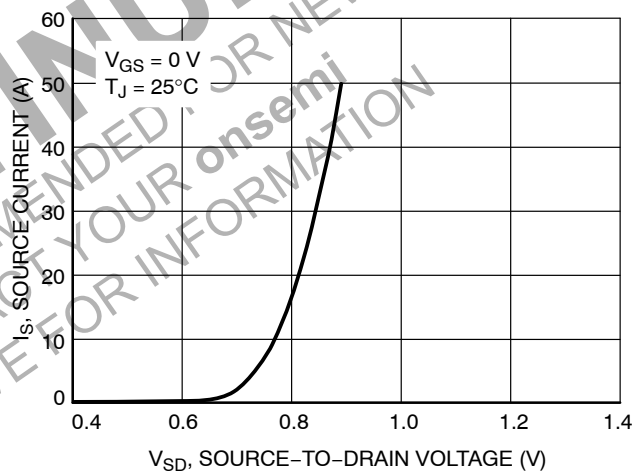


Figure 10. Diode Forward Voltage vs. Current

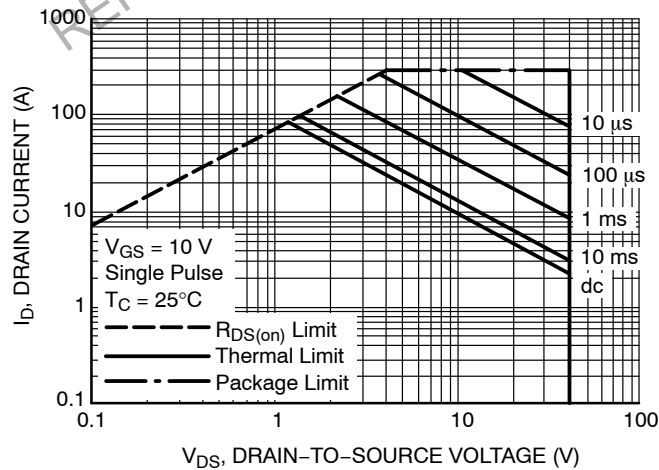


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL PERFORMANCE CHARACTERISTICS

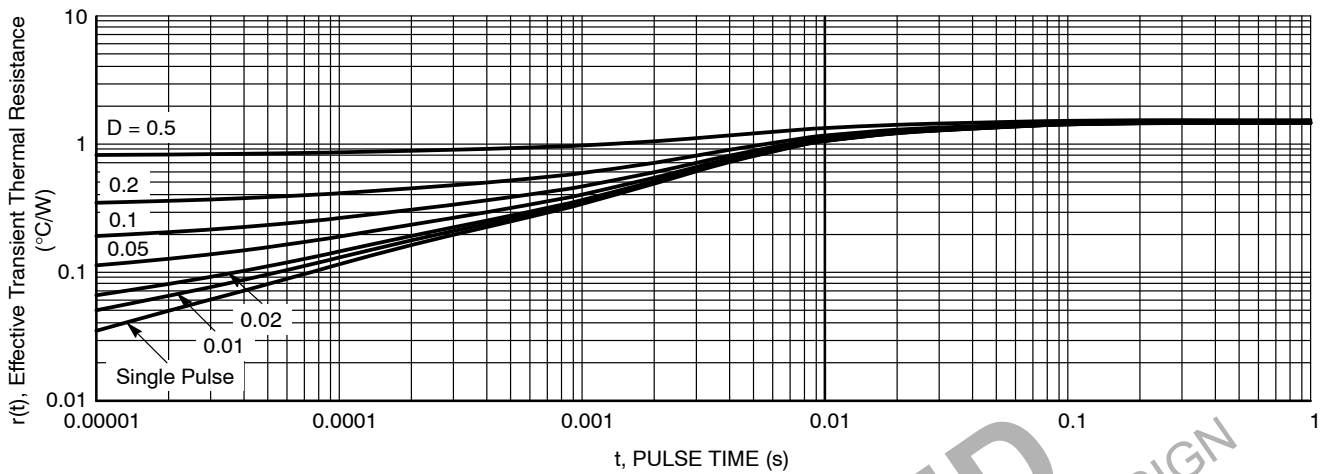


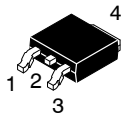
Figure 12. Thermal Response

ORDERING INFORMATION

| Order Number | Package           | Shipping <sup>†</sup> |
|--------------|-------------------|-----------------------|
| NTD5802NT4G  | DPAK<br>(Pb-Free) | 2500 / Tape & Reel    |
| NVD5802NT4G* | DPAK<br>(Pb-Free) | 2500 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

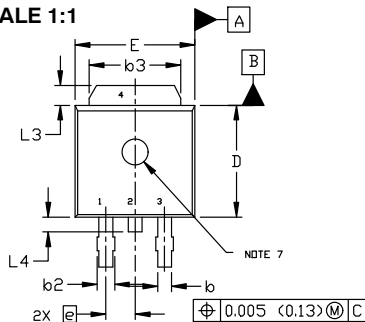
\*NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



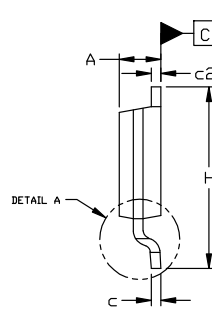
DPAK (SINGLE GAUGE)  
CASE 369C  
ISSUE G

DATE 31 MAY 2023

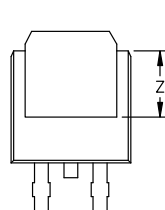
SCALE 1:1



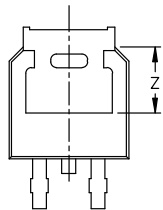
TOP VIEW



SIDE VIEW

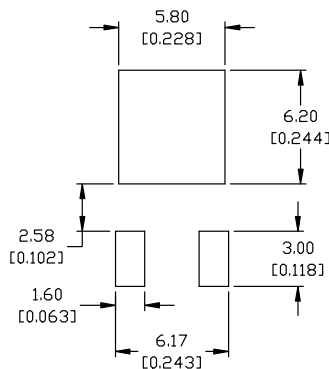


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE  
CONSTRUCTIONS



RECOMMENDED MOUNTING FOOTPRINT\*

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:

PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:

PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 3:

PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 4:

PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 5:

PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 6:

PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2

STYLE 7:

PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 8:

PIN 1. N/C  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 9:

PIN 1. ANODE  
2. CATHODE  
3. RESISTOR ADJUST  
4. CATHODE

STYLE 10:

PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

NOTES:

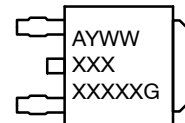
1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN.   | MAX.  | MIN.        | MAX.  |
| A   | 0.086  | 0.094 | 2.18        | 2.38  |
| A1  | 0.000  | 0.005 | 0.00        | 0.13  |
| b   | 0.025  | 0.035 | 0.63        | 0.89  |
| b2  | 0.028  | 0.045 | 0.72        | 1.14  |
| b3  | 0.180  | 0.215 | 4.57        | 5.46  |
| c   | 0.018  | 0.024 | 0.46        | 0.61  |
| c2  | 0.018  | 0.024 | 0.46        | 0.61  |
| D   | 0.235  | 0.245 | 5.97        | 6.22  |
| E   | 0.250  | 0.265 | 6.35        | 6.73  |
| e   | 0.090  | BSC   | 2.29        | BSC   |
| H   | 0.370  | 0.410 | 9.40        | 10.41 |
| L   | 0.055  | 0.070 | 1.40        | 1.78  |
| L1  | 0.114  | REF   | 2.90        | REF   |
| L2  | 0.020  | BSC   | 0.51        | BSC   |
| L3  | 0.035  | 0.050 | 0.89        | 1.27  |
| L4  | ----   | 0.040 | ---         | 1.01  |
| Z   | 0.155  | ----  | 3.93        | ---   |

GENERIC  
MARKING DIAGRAM\*



IC



Discrete

XXXXXX = Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

|                  |                     |                                                                                                                                                                                     |
|------------------|---------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| DESCRIPTION:     | DPAK (SINGLE GAUGE) | PAGE 1 OF 1                                                                                                                                                                         |

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